

	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	271357	257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	9171	1 and (TFT or (thin near film near transistor) or thin-film-transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	105	2 and (source near (electrode and bus))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	100	3 and drain near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L6	5	5 and edge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L7	3	6 and (perpendicular or inlin\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L5	14	4 and (first and second) near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L8	19	hatta-yoshihisa.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	19152	(TFT or (thin near film near transistor) or thin-film-transistor).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L10	58	9 and (source near (electrode and bus))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L11	53	10 and drain near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	L12	12	11 and (perpendicular or inlin\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	BRS	L13	55482	(TFT or (thin near film near transistor) or thin-film-transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
14	BRS	L14	327	13 and (source near (electrode and bus))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
15	BRS	L15	293	14 and drain near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
16	BRS	L16	50	15 and (first and second) near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
17	BRS	L17	0	16 and (perpendicular or inlin\$3) near edge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
18	BRS	L18	19	16 and edge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	